

Radiation	Type	Technology	Electrodes
Red	Point Source	AlInGaP/GaAs	N (cathode) up

	typ. dimensions (μm)	
	<u>typ. thickness</u> 170 (± 20) μm <u>cathode</u> gold alloy, 1.5 μm <u>anode</u> gold alloy, 0.5 μm	

Maximum Ratings

$T_{\text{amb}} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward current (DC)		I_F			35	mA

Optical and Electrical Characteristics

$T_{\text{amb}} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 5 \text{ mA}$	V_F		1.85	2.4	V
Reverse voltage	$I_R = 10 \mu\text{A}$	V_R	4			V
Radiant power*	$I_F = 5 \text{ mA}$	Φ_e	100	200		μW
Luminous intensity*	$I_F = 5 \text{ mA}$	I_V	5	7		mcd
Peak wavelength	$I_F = 5 \text{ mA}$	λ_p		645		nm
Spectral bandwidth at 50%	$I_F = 5 \text{ mA}$	$\Delta\lambda_{0.5}$		26		nm
Switching time	$I_F = 5 \text{ mA}$	t_r, t_f		40/30		ns

*Measured on bare chip on TO-18 header with *EPIGAP* equipment

Labeling

Type	Lot N°	$I_V(\text{typ})$ [mcd]	$V_F(\text{typ})$ [V]	Quantity
ELC-645-29-50				

Packing: Chips on adhesive film with wire-bond side on top